



# HLB123T

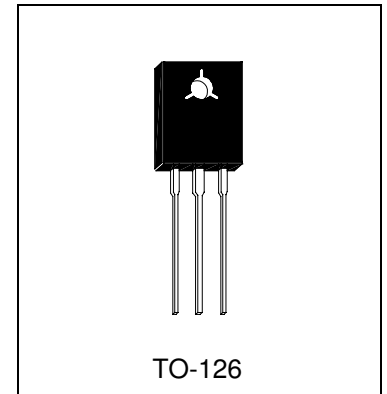
NPN EPITAXIAL PLANAR TRANSISTOR

## Description

The HLB123T is designed for high voltage. High speed switching inductive circuits and amplifier applications.

## Features

- High Speed Switching
- Low Saturation Voltage
- High Reliability



## Absolute Maximum Ratings (T<sub>A</sub>=25°C)

- Maximum Temperatures
  - Storage Temperature ..... -50 ~ +150 °C
  - Junction Temperature ..... +150 °C Maximum
- Maximum Power Dissipation
  - Total Power Dissipation (T<sub>A</sub>=25°C) ..... 3.5 W
  - Total Power Dissipation (T<sub>C</sub>=25°C) ..... 30 W
- Maximum Voltages and Currents
  - BV<sub>CBO</sub> Collector to Base Voltage ..... 600 V
  - BV<sub>CEO</sub> Collector to Emitter Voltage ..... 400 V
  - BV<sub>EBO</sub> Emitter to Base Voltage ..... 8 V
  - I<sub>C</sub> Collector Current (DC) ..... 1 A
  - I<sub>C</sub> Collector Current (Pulse) ..... 2 A

## Electrical Characteristics (T<sub>A</sub>=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	600	-	-	V	I <sub>C</sub> =1mA, I <sub>E</sub> =0
BV <sub>CEO</sub>	400	-	-	V	I <sub>C</sub> =10mA, I <sub>B</sub> =0
BV <sub>EBO</sub>	8	-	-	V	I <sub>E</sub> =1mA, I <sub>C</sub> =0
I <sub>CBO</sub>	-	-	10	uA	V <sub>CB</sub> =600V, I <sub>E</sub> =0
I <sub>EBO</sub>	-	-	10	uA	V <sub>BE</sub> =9V, I <sub>C</sub> =0
*V <sub>CE(sat)1</sub>	-	-	0.8	V	I <sub>C</sub> =0.1A, I <sub>B</sub> =10mA
*V <sub>CE(sat)2</sub>	-	-	0.9	V	I <sub>C</sub> =0.3A, I <sub>B</sub> =30mA
*V <sub>BE(sat)1</sub>	-	-	1.2	V	I <sub>C</sub> =0.1A, I <sub>B</sub> =10mA
*V <sub>BE(sat)2</sub>	-	-	1.8	V	I <sub>C</sub> =0.3A, I <sub>B</sub> =30mA
*h <sub>FE1</sub>	13	-	27		I <sub>C</sub> =0.3A, V <sub>CE</sub> =5V
*h <sub>FE2</sub>	10	-	-		I <sub>C</sub> =0.5A, V <sub>CE</sub> =5V
*h <sub>FE3</sub>	6	-	-		I <sub>C</sub> =1A, V <sub>CE</sub> =5V

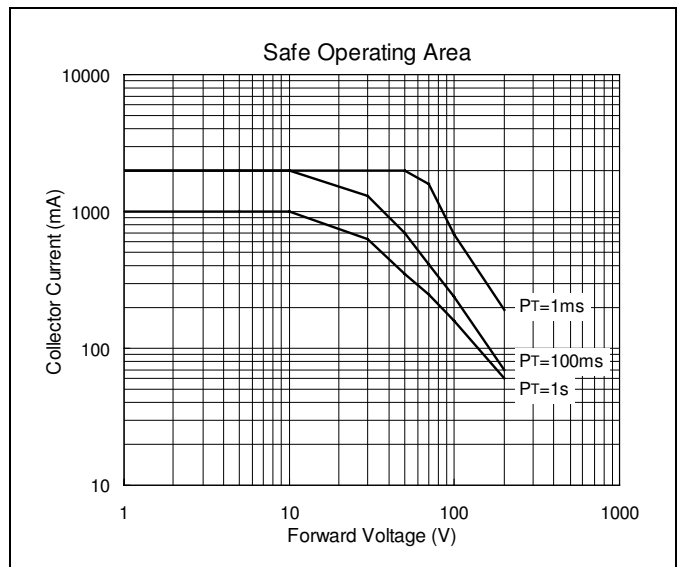
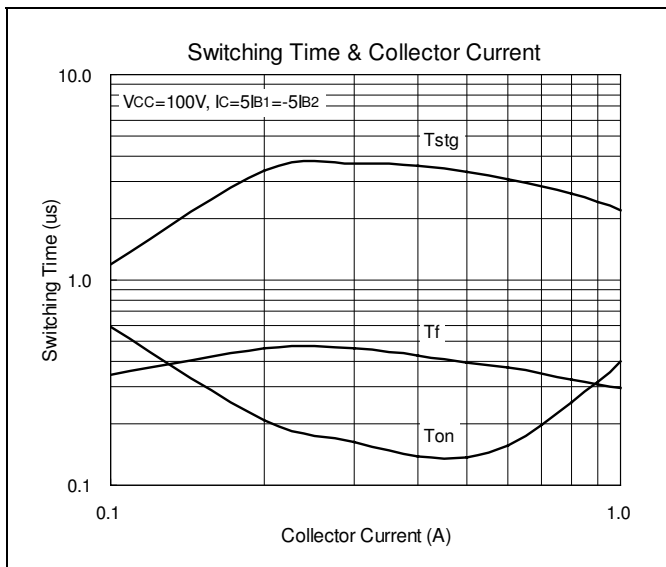
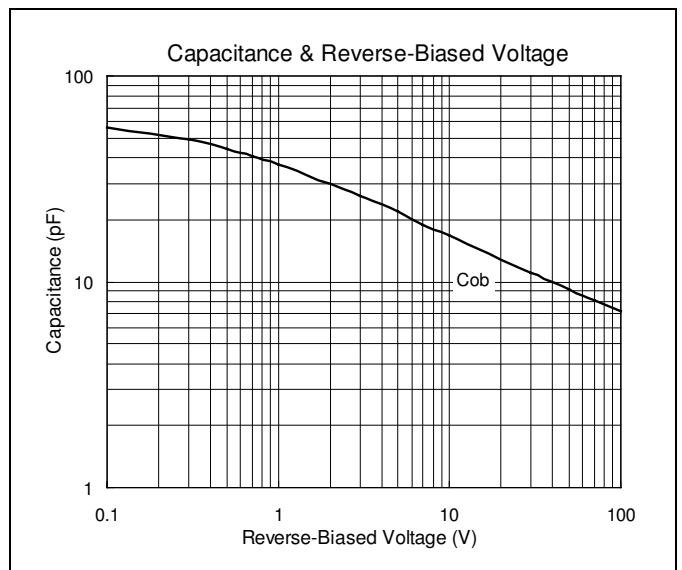
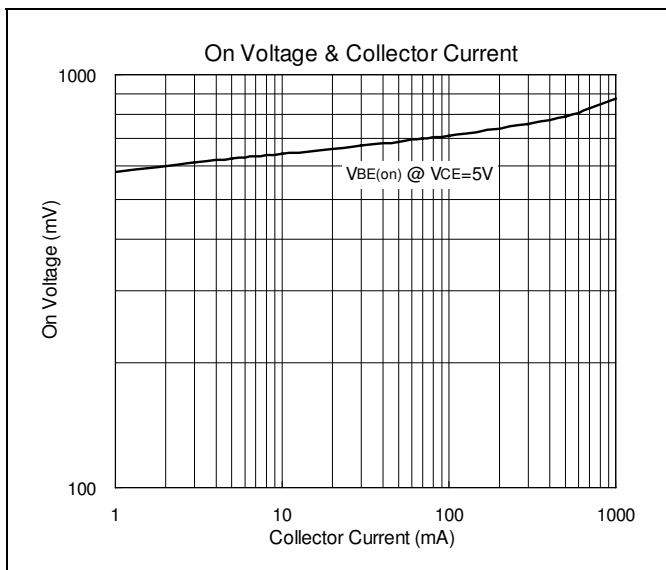
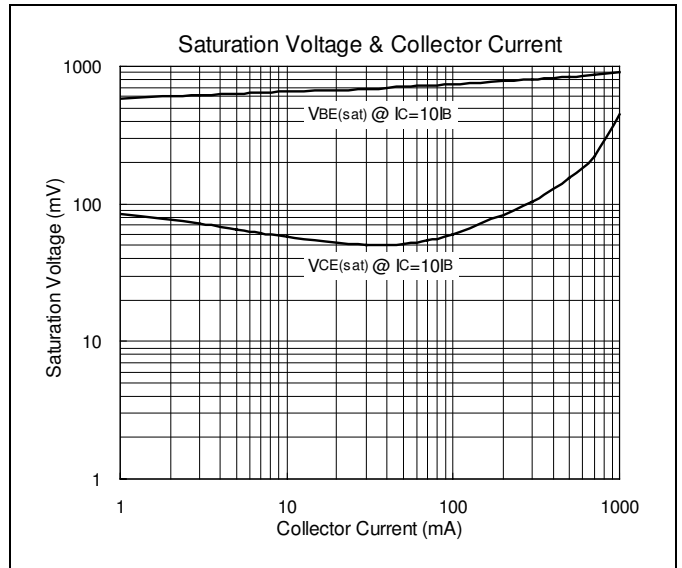
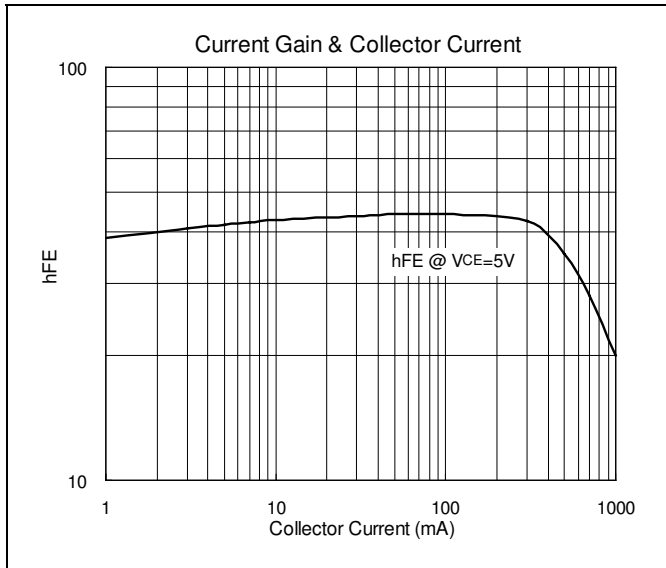
\*Pulse Test: Pulse Width ≤380us, Duty Cycle ≤2%

## Classification Of hFE1

Rank	B2	B3
Range	13-22	18-27



### Characteristics Curve





### TO-126 Dimension

3-Lead TO-126  
 Plastic Package  
 HSMC Package Code: T

Marking:

Pb Free Mark  
 Pb-Free: "•" (Note)  
 Normal: None

Date Code      Control Code

Note: Green label is used for pb-free packing  
 Pin Style: 1.Emitter 2.Collector 3.Base

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	3.60	4.40
B	6.90	7.60
C	13.00	16.50
D	7.20	8.50
F	0.65	0.88
G	1.00	1.42
H	4.52	4.62
J	1.14	1.50
K	0.90	1.50
L	0.45	0.60
M	2.92	3.40
N	2.00	2.70

Unit: mm

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#### Head Office And Factory:

- **Head Office** (Hi-Sincerity Microelectronics Corp.): 10F., No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C.  
 Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- **Factory 1:** No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C  
 Tel: 886-3-5983621~5 Fax: 886-3-5982931



### Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T <sub>smin</sub> )	100°C	150°C
- Temperature Max (T <sub>smax</sub> )	150°C	200°C
- Time (min to max) (ts)	60~120 sec	60~180 sec
T <sub>smax</sub> to T <sub>L</sub>		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60~150 sec	60~150 sec
Peak Temperature (T <sub>p</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t <sub>p</sub> )	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	10sec ±1sec
Pb-Free devices.	260°C ±5°C	10sec ±1sec